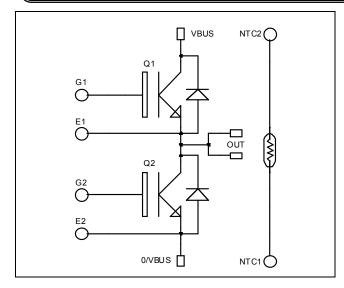
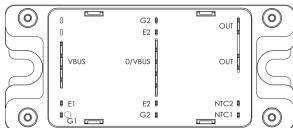


Phase leg High speed Trench + Field Stop IGBT4 Power Module







Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- Lead frames for power connections
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- RoHS Compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25$ °C	250	
I_{C}	Continuous Collector Current $T_C = 80^{\circ}C$	$T_C = 80$ °C	150	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	480	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation		750	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				100	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C	1.78	2.05	2.4	V
$V_{CE(sat)}$	Confector Emitter Saturation Voltage	$I_C = 150A$ $T_j = 150^{\circ}C$			2.6		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 5.2 \text{ mA}$		5.3	5.8	6.3	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				240	nA

Dynamic Characteristics (Per IGBT)

•	Characteristic	Test Condition	ns	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			8.8		
C_{oes}	Output Capacitance	$V_{CE} = 25V$			0.5		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.45		
Q_{G}	Gate charge	$V_{GE} = 15V, I_{C} = 150A$ $V_{CE} = 960V$			645		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$			30		
T_{r}	Rise Time				57		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$			290		ns
T_{f}	Fall Time	$R_G = 3.5\Omega$	~		16		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)			30		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			49		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 150A$ $R_{\text{G}} = 3.5\Omega$			366		ns
T_{f}	Fall Time				48		
E_{on}	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 150$ °C		13		mJ
E_{off}	Turn off Energy	$I_C = 150A$ $R_G = 3.5\Omega$	$T_j = 150$ °C		8		111,)
R_G	Integrated gate resistor				5		Ω
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 600V$ $t_p \le 10\mu s$; $T_j = 150$ °C			525		A
R_{thJC}	Junction to Case Thermal Resistance		·			0.20	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$				400	μΑ
I_F	DC Forward Current		$Tc = 60^{\circ}C$		120		A
		$I_{\rm F} = 120A$			2.6	3.5	
V_{F}	Diode Forward Voltage	$I_F = 240A$			3.2		V
		$I_{\rm F} = 120A$	$T_{j} = 125^{\circ}C$		1.8		
+	Daviana Dagayany Tima	$I_F = 120A$	$T_j = 25$ °C		300		na
t _{rr}	Reverse Recovery Time		1 1; - 12.3 C		380		ns
Q _{rr}	Reverse Recovery Charge	$\begin{array}{c} V_R = 800V \\ di/dt = 800A/\mu s \end{array}$	$T_j = 25^{\circ}C$		1.44		uС
			$T_{j} = 125^{\circ}C$		6.8		μС
R_{thJC}	Junction to Case Thermal Resistance				0.33	°C/W	



Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

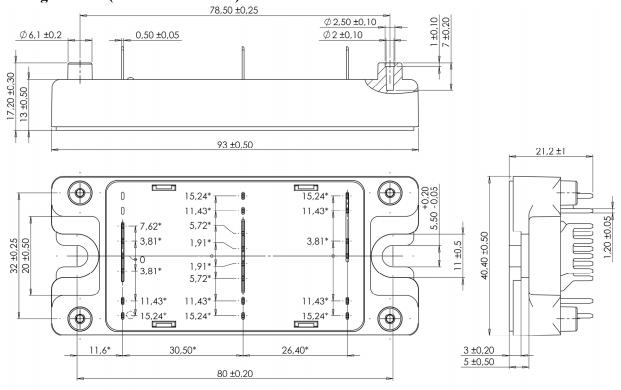
Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[\frac{1}{B_{25/85}} \left(\frac{1}{T_{-1}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	C
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

Package outline (dimensions in mm)

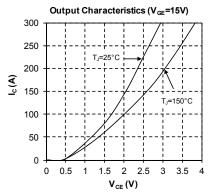


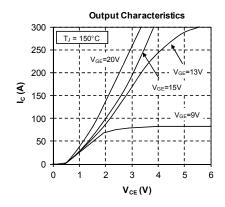
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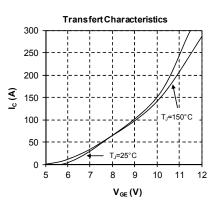
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

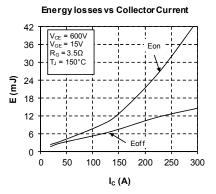


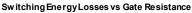
Typical performance curve

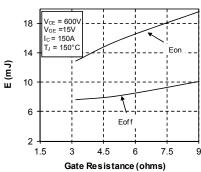


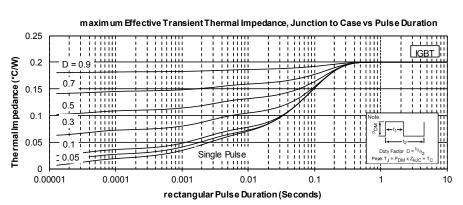






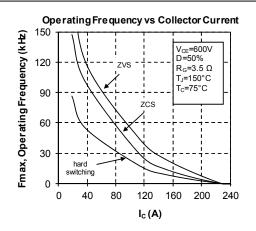


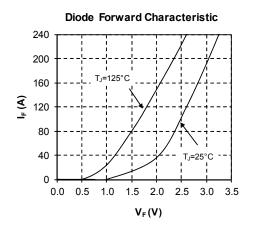




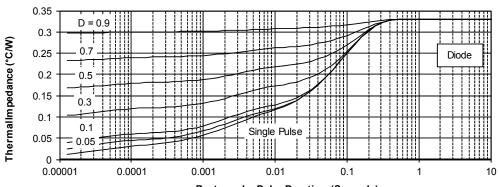


Power Matters.™





maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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